

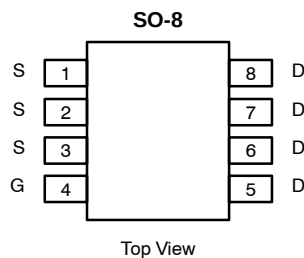
N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

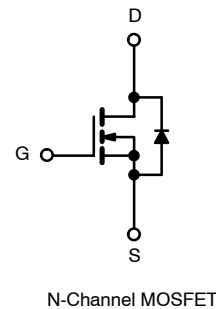
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.024 @ $V_{GS} = 10$ V	8.1
	0.033 @ $V_{GS} = 4.5$ V	6.9

FEATURES

- TrenchFET® Power MOSFETS



Ordering Information: Si9410BDY
Si9410BDY-T1 (with Tape and Reel)
Si9410BDY—E3 (Lead (Pb)-Free)
Si9410BDY-T1—E3 (Lead (Pb)-Free with Tape and Reel)



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V _{DS}	30		V
Gate-Source Voltage		V _{GS}	±20		
Continuous Drain Current (T _J = 150°C) ^a	T _A = 25°C	I _D	8.1	6.2	A
	T _A = 70°C		6.5	5.0	
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	30		
Continuous Source Current (Diode Conduction) ^a		I _S	2.1	1.2	
Maximum Power Dissipation ^a	T _A = 25°C	P _D	2.5	1.5	W
	T _A = 70°C		1.6	0.9	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	R_{thJA}	40	50	$^\circ\text{C/W}$
	Steady State		70	85	
Maximum Junction-to-Foot	Steady State	R_{thJF}	20	24	

Notes

a. Surface Mounted on 1" x 1" FR4 Board.

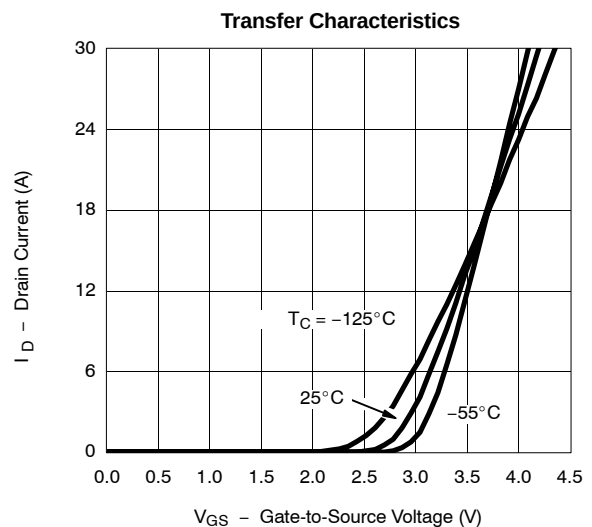
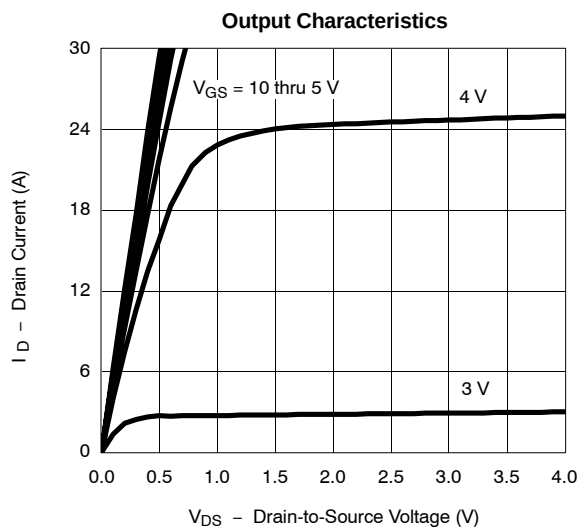
SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\ \mu\text{A}$	1.0		3.0	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}$, $V_{GS} = \pm 20\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30\ \text{V}$, $V_{GS} = 0\ \text{V}$			1	μA
		$V_{DS} = 30\ \text{V}$, $V_{GS} = 0\ \text{V}$, $T_J = 55^\circ\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\ \text{V}$, $V_{GS} = 10\ \text{V}$	30			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = 10\ \text{V}$, $I_D = 8.1\ \text{A}$		0.019	0.024	Ω
		$V_{GS} = 4.5\ \text{V}$, $I_D = 6.9\ \text{A}$		0.026	0.033	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\ \text{V}$, $I_D = 8.1\ \text{A}$		20		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.1\ \text{A}$, $V_{GS} = 0\ \text{V}$		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 15\ \text{V}$, $V_{GS} = 10\ \text{V}$, $I_D = 8.1\ \text{A}$		15	23	nC
Gate-Source Charge	Q_{gs}			3.2		
Gate-Drain Charge	Q_{gd}			2.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\ \text{V}$, $R_L = 15\ \Omega$ $I_D \cong 1\ \text{A}$, $V_{GEN} = 10\ \text{V}$, $R_g = 6\ \Omega$		10	15	ns
Rise Time	t_r			15	25	
Turn-Off Delay Time	$t_{d(off)}$			30	45	
Fall Time	t_f			11	20	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.1\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$		25	50	

Notes

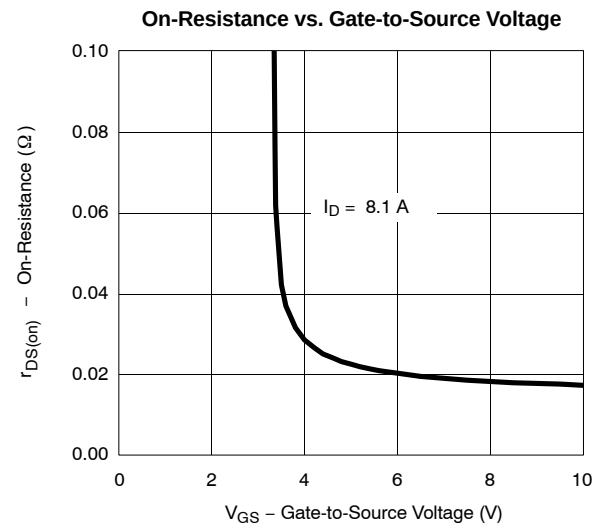
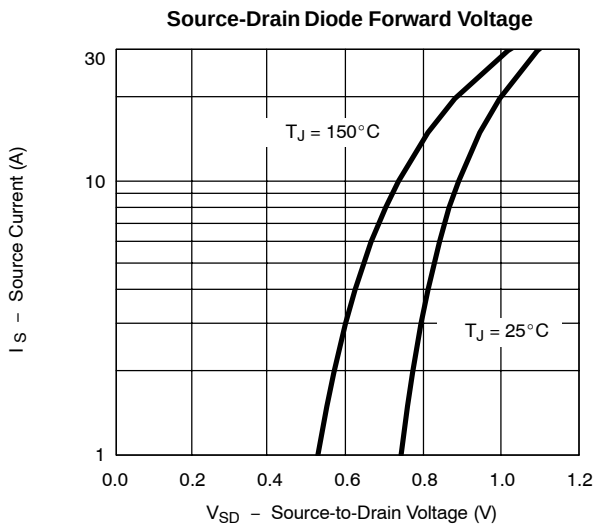
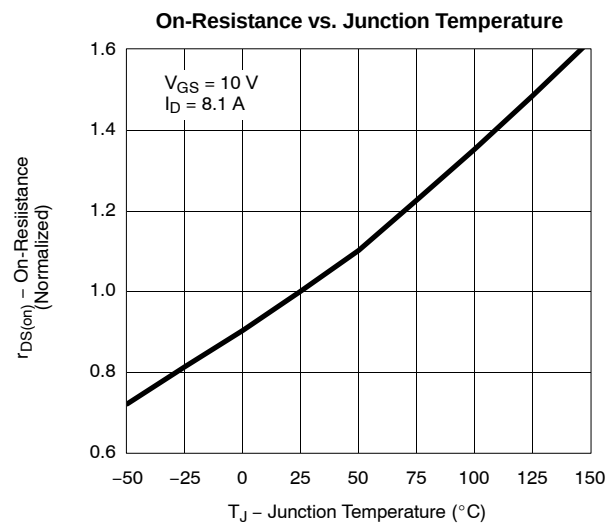
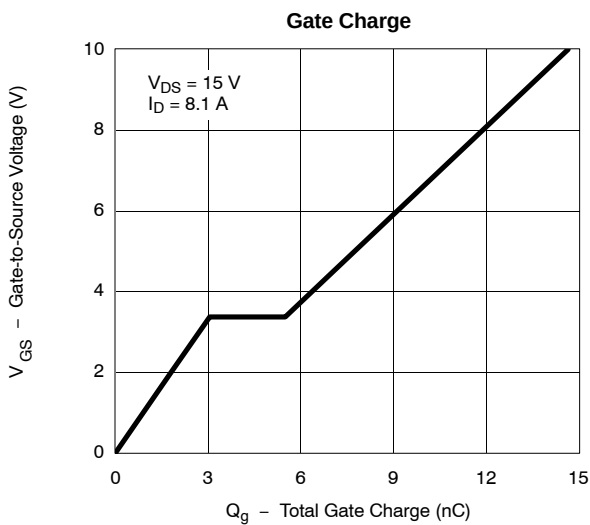
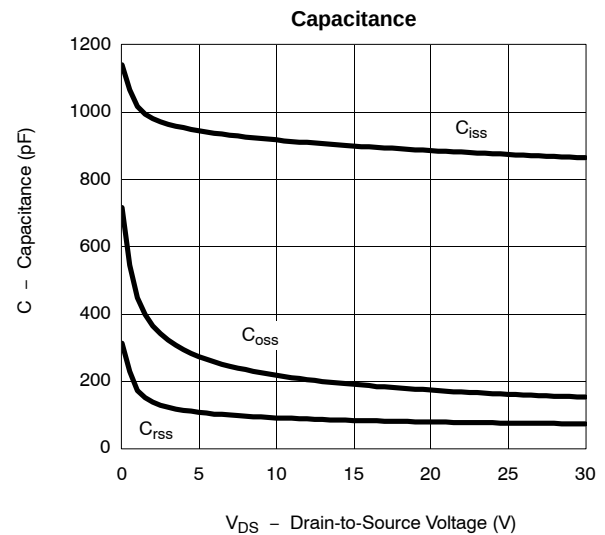
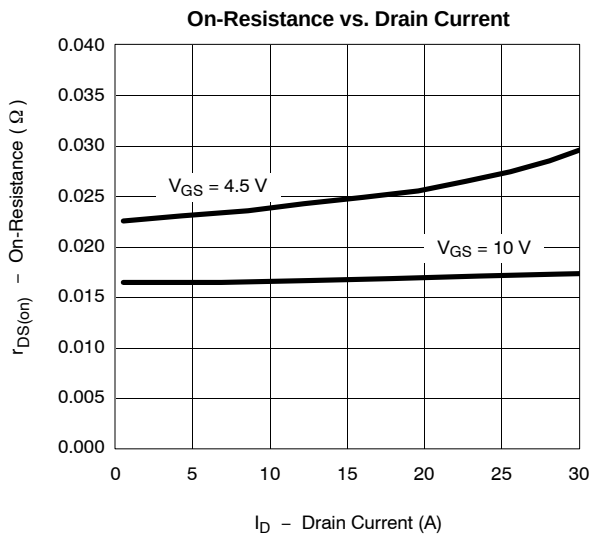
- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

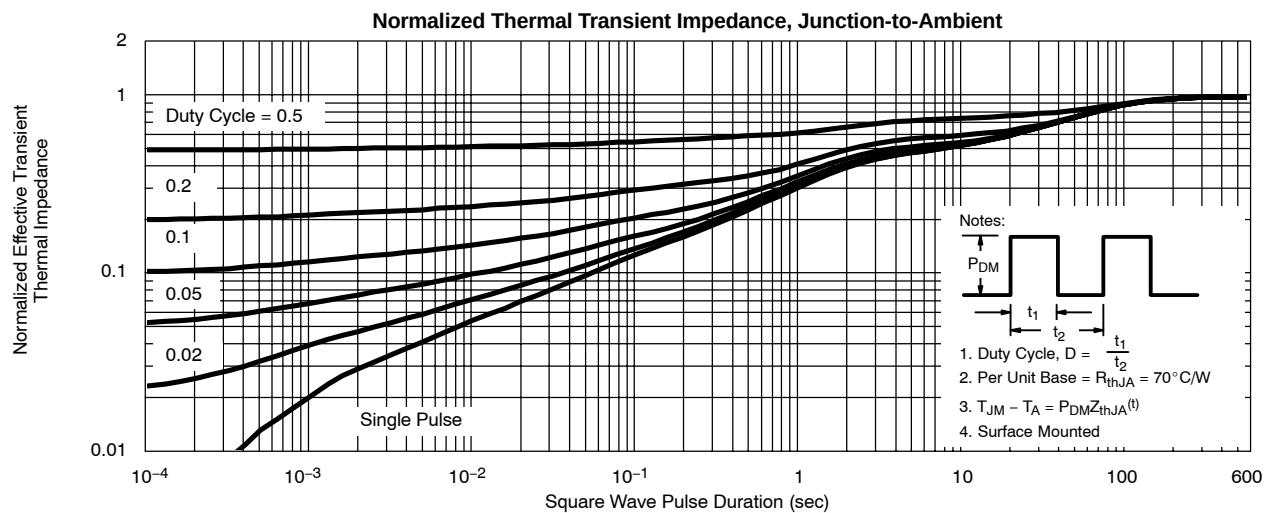
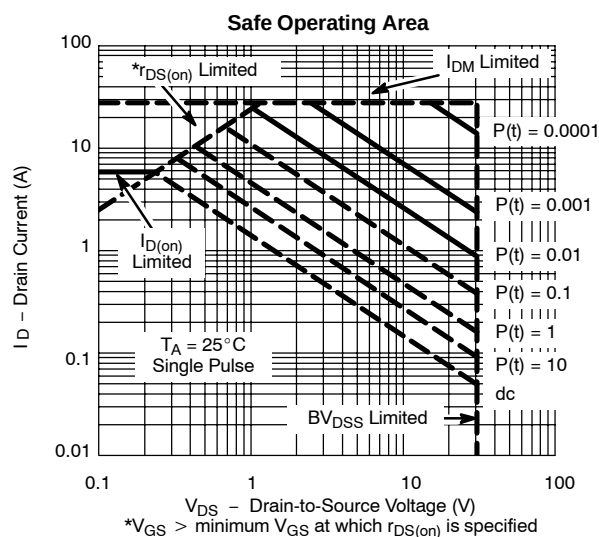
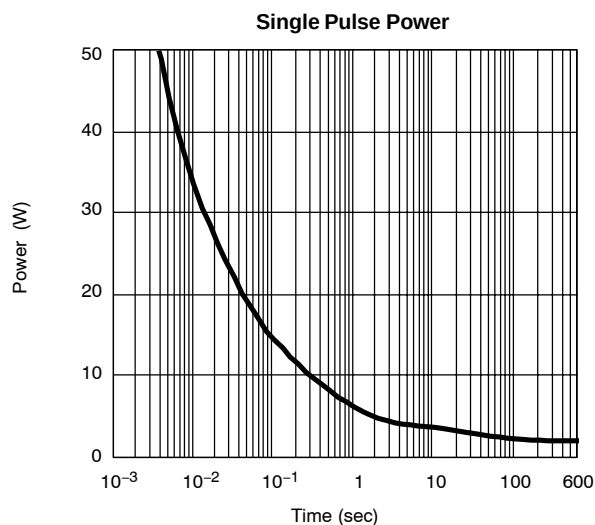
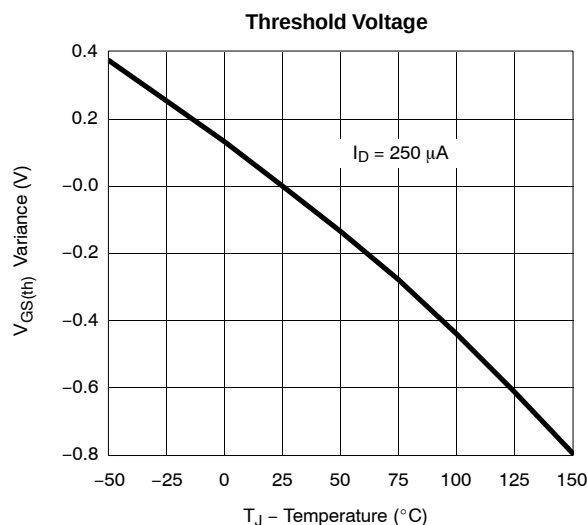
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)



TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

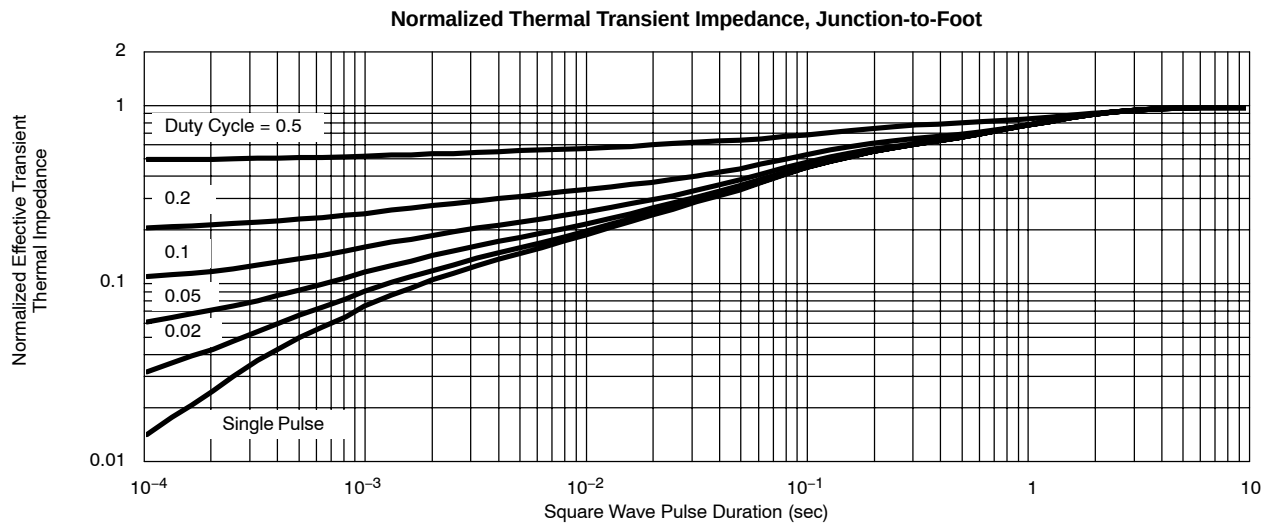


TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)





TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg?72269>.